

**isc Silicon PNP Power Transistors**

**2SB655**

**DESCRIPTION**

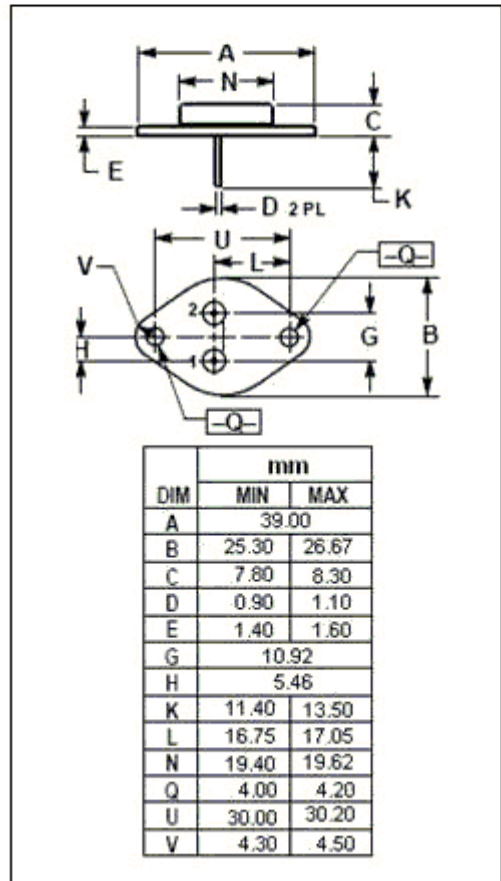
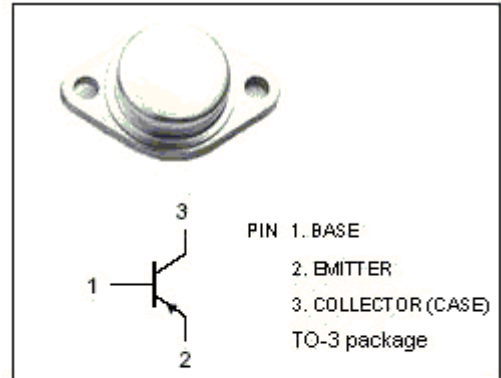
- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = -160V(\text{Min})$
- High Power Dissipation-  
:  $P_C = 100W(\text{Max})@T_C=25^\circ\text{C}$
- Complement to Type 2SD675

**APPLICATIONS**

- Designed for low frequency power amplifier applications.

**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-160	V
$V_{CEO}$	Collector-Emitter Voltage	-160	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current-Continuous	-12	A
$I_{CM}$	Collector Current-Peak	-20	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	100	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55~150	$^\circ\text{C}$



**isc Silicon PNP Power Transistors****2SB655****ELECTRICAL CHARACTERISTICS**T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -50mA; R <sub>BE</sub> = ∞	-160			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = -5mA; I <sub>C</sub> = 0	-5			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -6A; I <sub>B</sub> = -0.6A			-2.5	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = -1A; V <sub>CE</sub> = -5V			-1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -120V; I <sub>E</sub> = 0			-0.1	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -1A; V <sub>CE</sub> = -5V	60		200	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -6A; V <sub>CE</sub> = -5V	20			
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = -1A; V <sub>CE</sub> = -5V		22		MHz

◆ **h<sub>FE</sub> Classifications**

B	C
60-120	100-200